

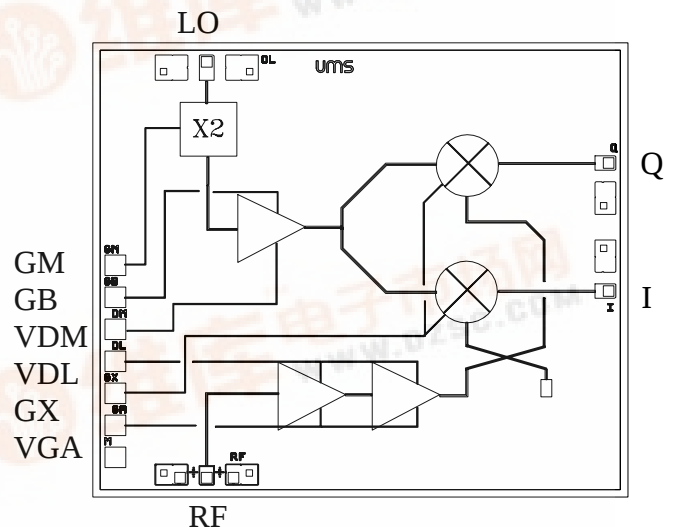
24-30GHz Integrated Down Converter

GaAs Monolithic Microwave IC

Description

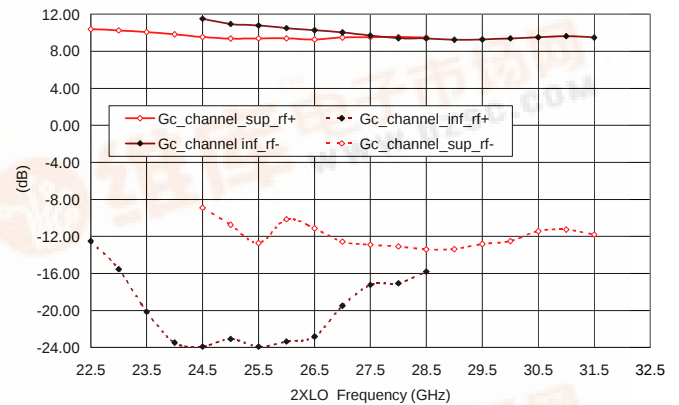
The CHR2295 is a multifunction chip which integrates a LO time two multiplier, a balanced cold FET mixer, and a RF LNA. It is designed for a wide range of applications, typically commercial communication systems. The backside of the chip is both RF and DC grounds. This helps simplify the assembly process.

The circuit is manufactured with a PM-HEMT process, 0.25μm gate length, via holes through the substrate, air bridges and electron beam gate lithography. It is available in chip form.



Main Features

- Broadband performances : 24-30GHz
- 11 dB conversion gain
- 3.5.0dB noise figure
- 10dBm LO input power
- -10dBm RF input power (1dB gain comp.)
- Low DC power consumption, 120mA@3.5V
- Chip size : 2.49 X 1.97 X 0.10 mm



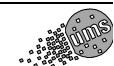
Conversion Gain & Image suppression @ IF=1.5GHz
(including test board losses)

Main Characteristics

Tamb. = 25°C

	Parameter	Min	Typ	Max	Unit
F_{RF}	RF frequency range	24		30	GHz
F_{LO}	LO frequency range	12		15	GHz
F_{IF}	IF frequency range	0.25		1.5	GHz
G_c	Conversion gain		11		dB

ESD Protection : Electrostatic discharge sensitive device. Observe handling precautions !



Electrical Characteristics for Broadband OperationT_{amb} = +25°C, V_d = 3.5V

Symbol	Parameter	Min	Typ	Max	Unit
F _{RF}	RF frequency range	24		30	GHz
F _{LO}	LO frequency range	12		15	GHz
F _{IF}	IF frequency range	0.25		1.5	GHz
G _c	Conversion gain (1)		11		dB
NF	Noise Figure		3.5		dB
P _{LO}	LO Input power		+10		dBm
Img Sup	Image Suppression		17		dBc
P1dB	Input power at 1dB gain compression		-10		dBm
LO VSWR	Input LO VSWR (1)		2.0:1		
RF VSWR	Input RF VSWR (1)		3.0:1		
I _d	Bias current (2)		120		mA

(1) On Wafer measurements

(2) Current source biasing network is recommended. Optimum performances for I_{dm}= 50mA and I_{dl}= 70mA**Absolute Maximum Ratings**T_{amb.} = 25°C (1)

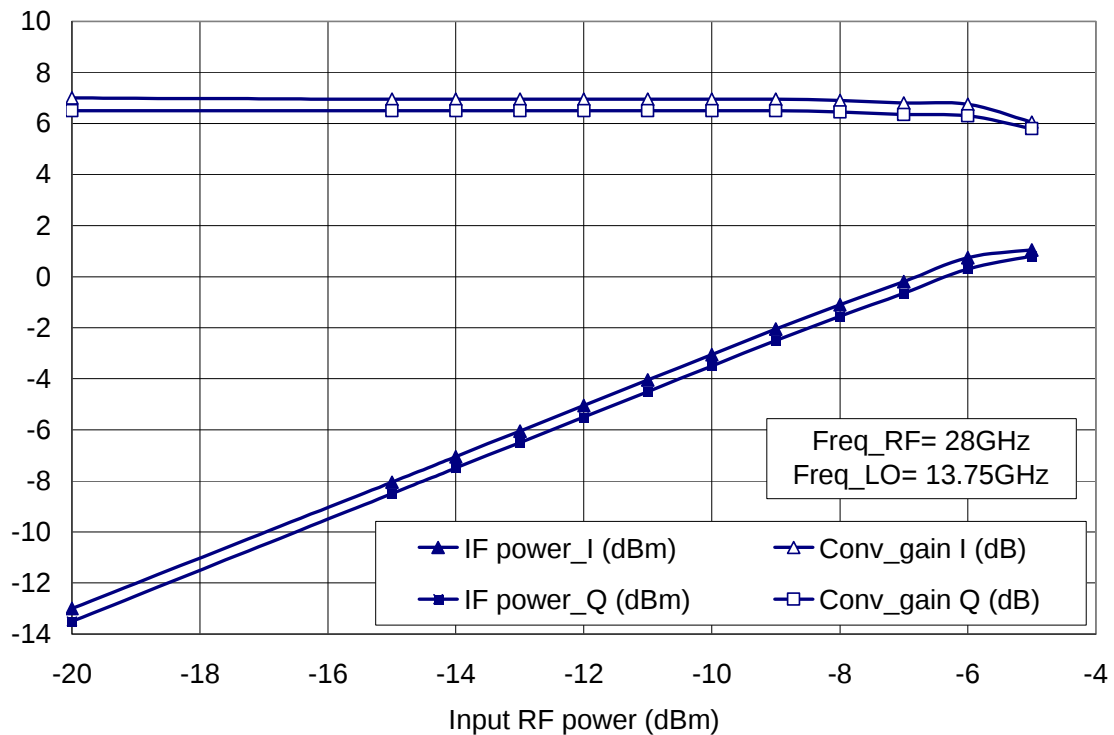
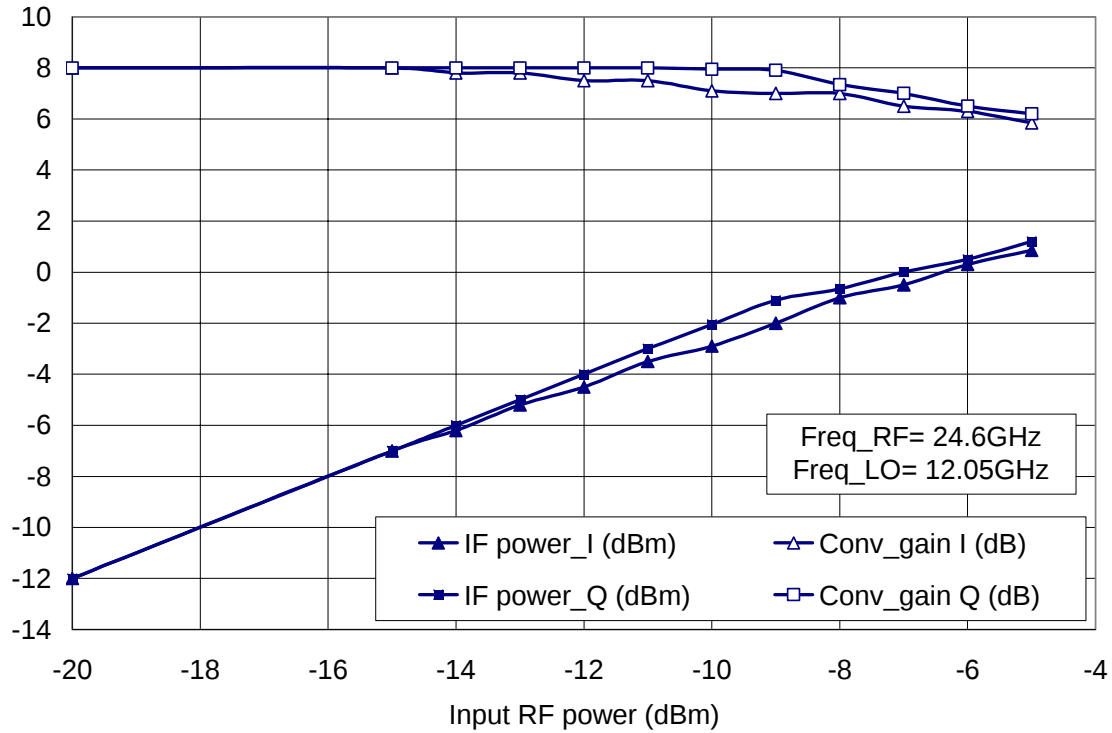
Symbol	Parameter	Values	Unit
V _d	Drain bias voltage	4.0	V
I _d	Drain bias current	200	mA
V _g	Gate bias voltage	-2.0 to +0.4	V
P _{in}	Maximum peak input power overdrive (2)	+15	dBm
T _a	Operating temperature range	-40 to +85	°C
T _{stg}	Storage temperature range	-55 to +155	°C

(1) Operation of this device above anyone of these parameters may cause permanent damage.

(2) Duration < 1s.

Typical On-wafer Measurements

Bias Conditions : $V_{dm} = V_{dl} = 3.5\text{ V}$, $V_{gm} = -0.9\text{ V}$, $V_{gb} = -0.3\text{ V}$, $V_{gx} = -0.7\text{ V}$, $V_{ga} = -0.2\text{ V}$

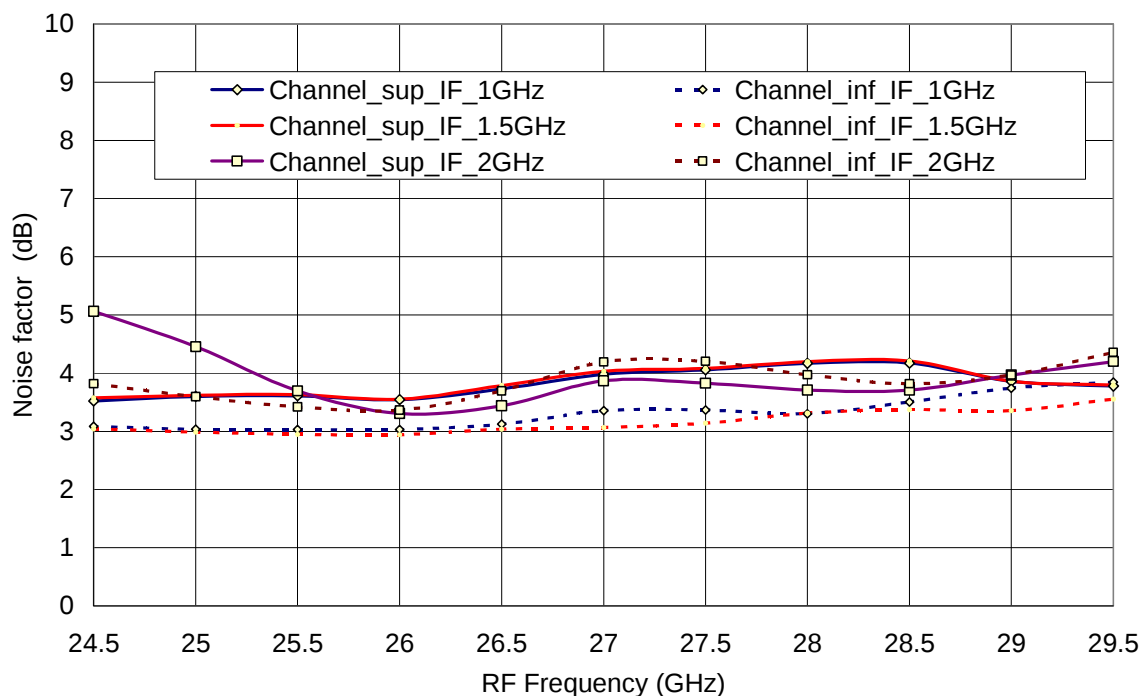
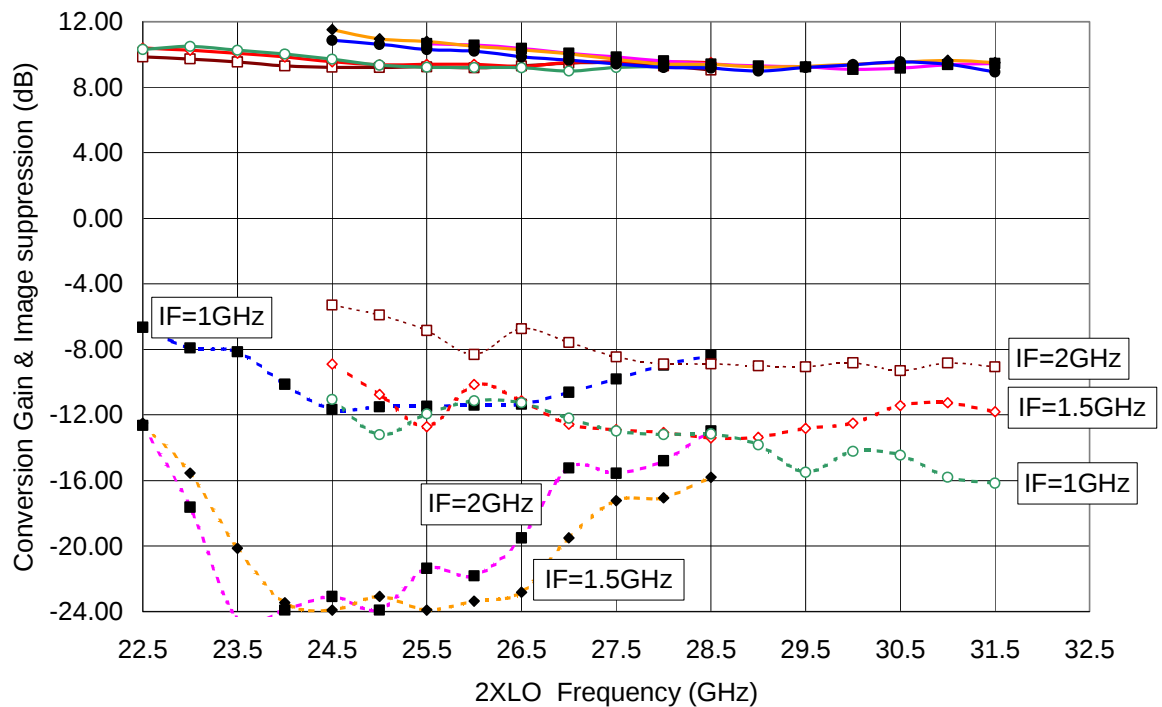


Input RF compression by channel

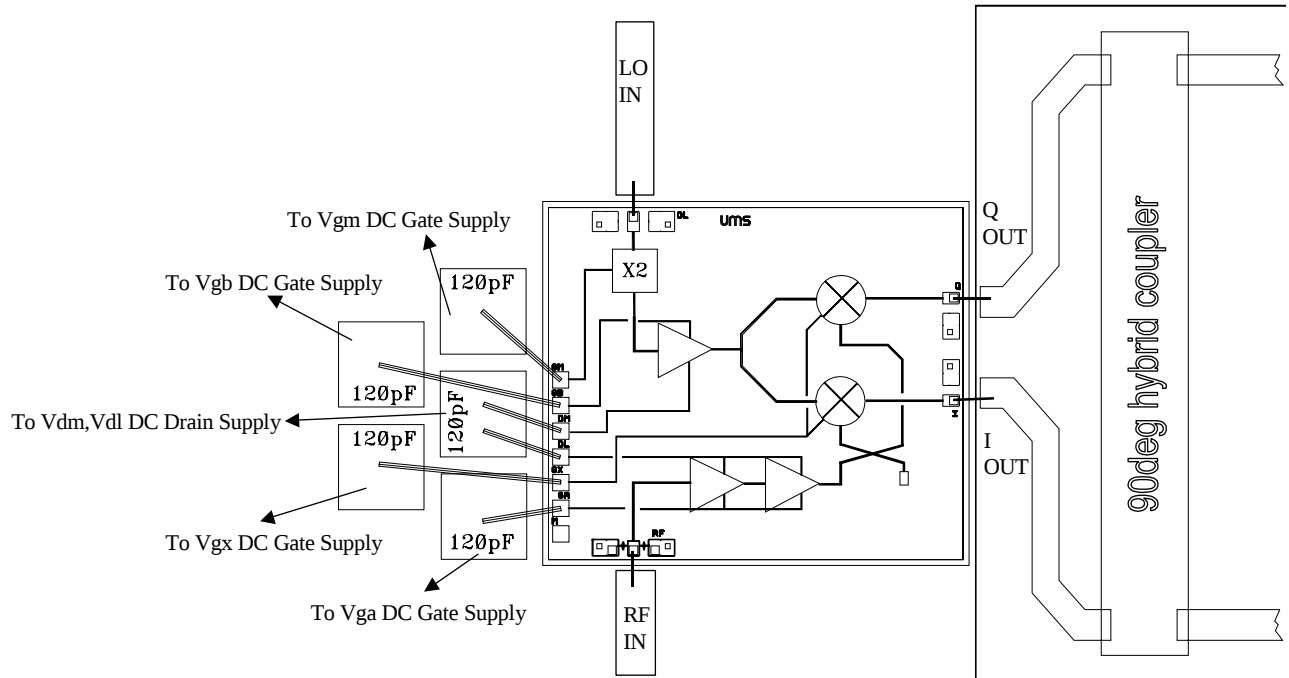
Typical On-board Measurements

Bias Conditions : $V_{dm} = V_{dl} = 3.5\text{ V}$, $V_{gm} = V_{gx} = -0.9\text{ V}$, $V_{gb} = V_{ga} = -0.3\text{ V}$

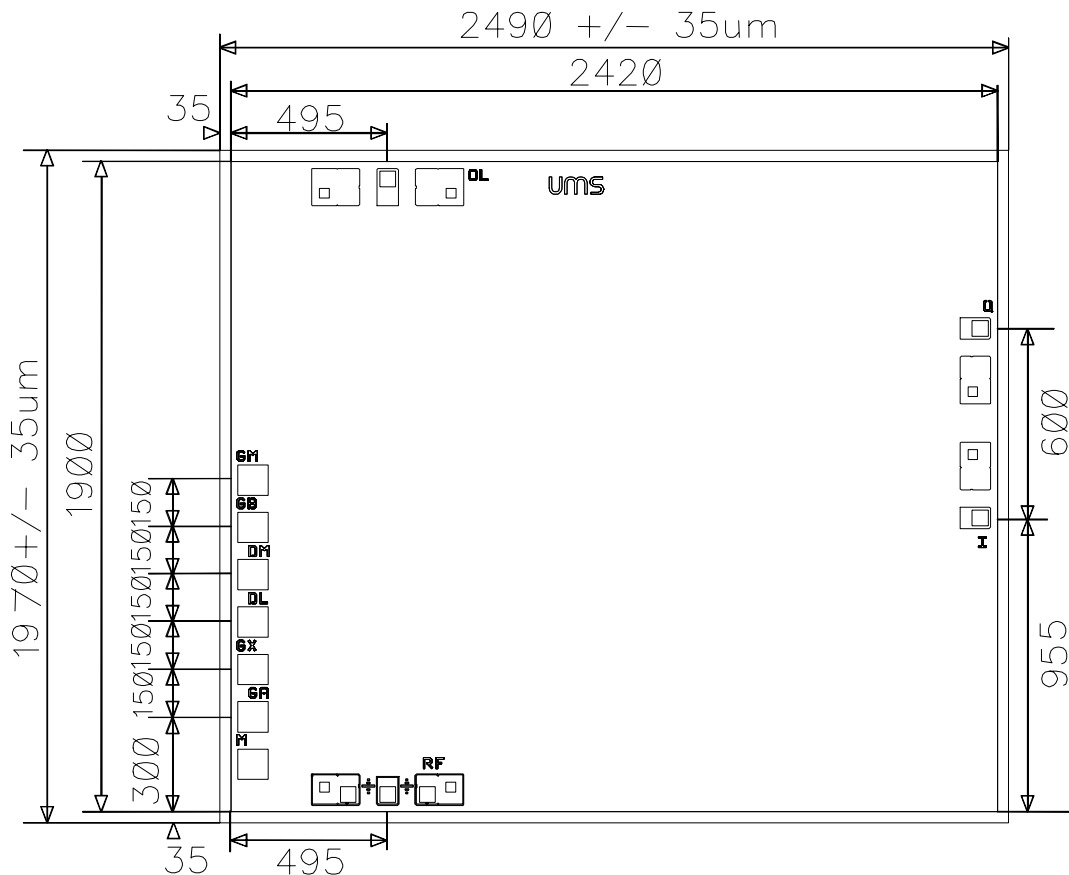
All these measurements include the losses from the test board (about 1dB on the conversion gain and 0.5dB on the noise figure).



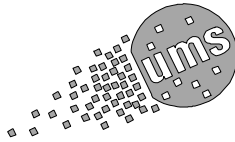
Chip Assembly and Mechanical Data



Note : Supply feed should be capacitively bypassed. 25µm diameter gold wire is recommended



Bonding pad positions
(Chip thickness : 100µm. All dimensions are in micrometers)



Ordering Information

Chip form : CHR2295-99F/00

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